

D45H5 D45H8 \ D45H11

PNP SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- LOW COLLECTOR-EMITTER SATURATION VOLTAGE
- FAST SWITCHING SPEED

APPLICATIONS

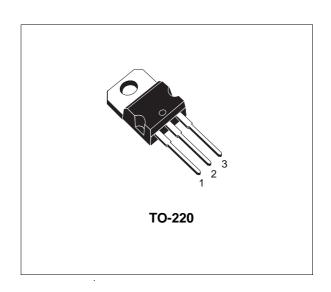
 GENERAL PURPOSE SWITCHING AND AMPLIFIER

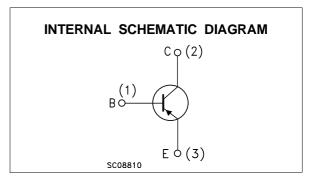
DESCRIPTION

The D45H5, D45H8 and D45H11 are silicon Multi-Epitaxial Planar PNP transistors mounted in Jedec TO-220 plastic package.

They are inteded for various switching and general purpose applications.

D45H8, D45H11 are complementary with D44H8, D44H11.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value					
		D45H5	D45H8	D45H11				
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	-45	-60	-80	V			
V_{EBO}	Emitter-Base Voltage (I _C = 0)		-5					
Ic	Collector Current		-10			-10		Α
I _{CM}	Collector Peak Current		-20					
I _B	Base Current		-5					
P _{tot}	Total Dissipation at T _c ≤ 25 °C		50					
T _{stg}	Storage Temperature		-65 to 150					
Tj	Max. Operating Junction Temperature	150			°C			

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D45H5/D45H8/D45H11

THERMAL DATA

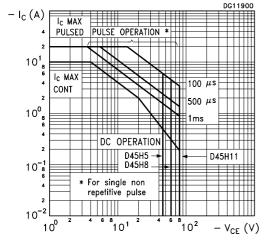
R _{thj-case} Thermal Resistance Junction-case	Max	2.5 °C/W	Junction-case	Resistance	Thermal	R _{thj-case}
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

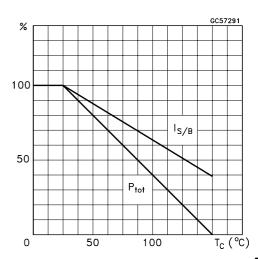
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = rated V _{CEO}			-10	μΑ
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = -5V			-100	μΑ
$V_{\text{CEO(sus)}^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = -100 mA for D45H5 for D45H8 for D45H11	-45 -60 -80			> >
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = -8 A I _B = -0.4 A I _C = -8 A I _B = -0.8 A			-1 -1	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$I_C = -8 \text{ A}$ $I_B = -0.8 \text{ A}$			-1.5	٧
h _{FE} *	DC Current Gain	I _C = -2 A	60 40	120 70		

^{*} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 2 %

Safe Operating Area



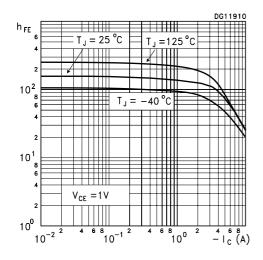
Derating Curves



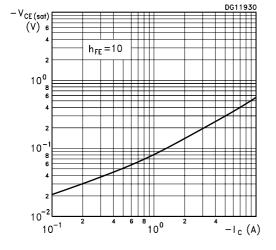
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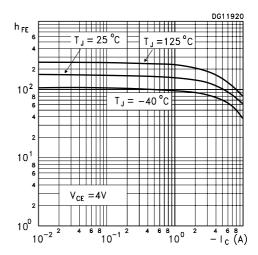
DC Current Gain



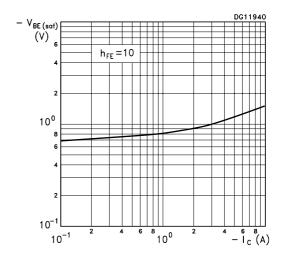
Collector-Emitter Saturation Voltage



DC Current Gain



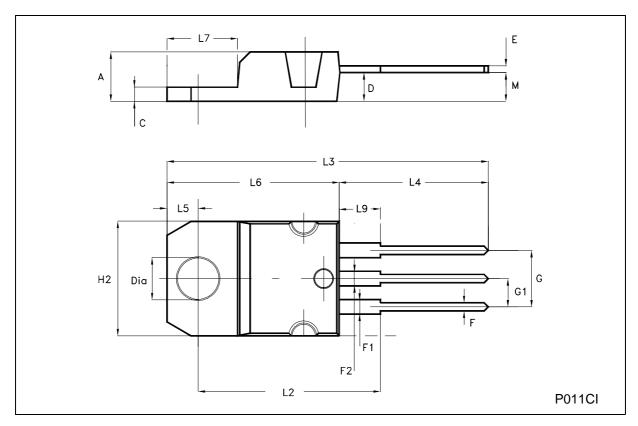
Base-Emitter Saturation Voltage



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TO-220 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.052	
D	2.40		2.72	0.094		0.107	
E	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.202	
G1	2.40		2.70	0.094		0.106	
H2	10.00		10.40	0.394		0.409	
L2		16.40			0.645		
L4	13.00		14.00	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.20		6.60	0.244		0.260	
L9	3.50		3.93	0.137		0.154	
M		2.60			0.102		
DIA.	3.75		3.85	0.147		0.151	



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